

Schottky barrier diode

• Application

Rectifying small power

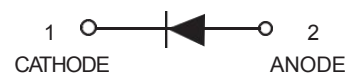
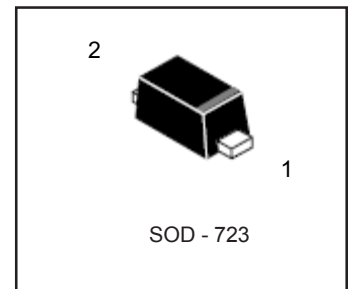
• Features

- 1) Ultra small mold type.
- 2) Low V_F
- 3) High reliability

• Construction

Silicon epitaxial planer

- z We declare that the material of product compliance with RoHS requirements.
- z We declare that the material of product is Halogen Free (Threen Epoxy Compound).



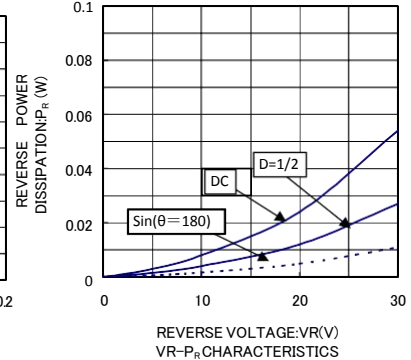
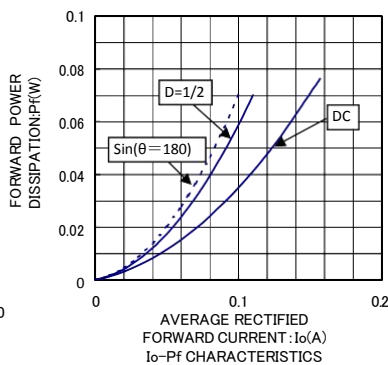
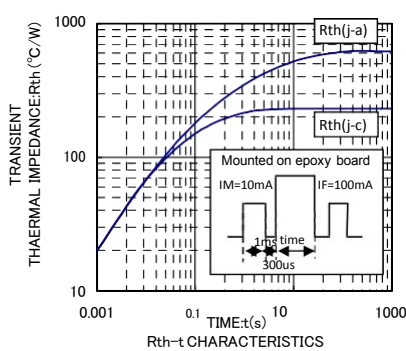
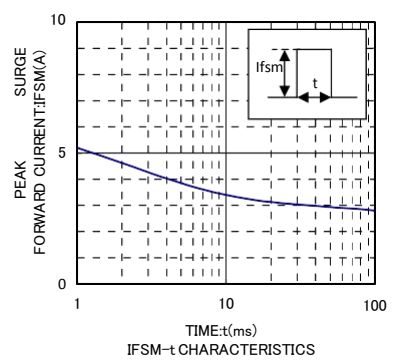
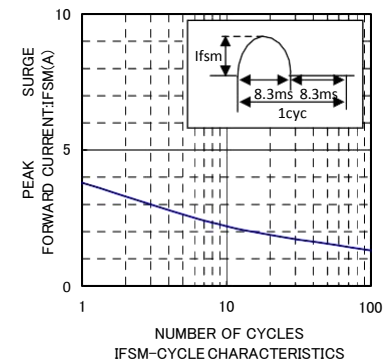
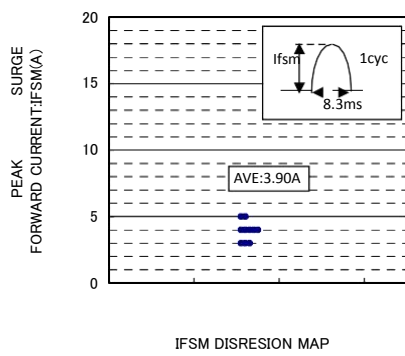
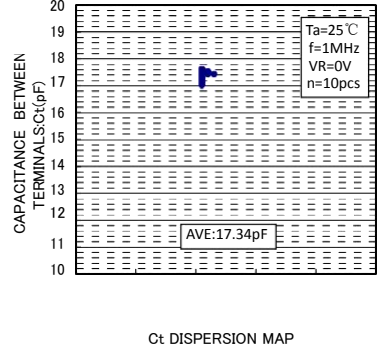
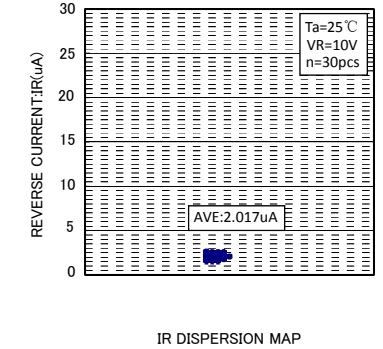
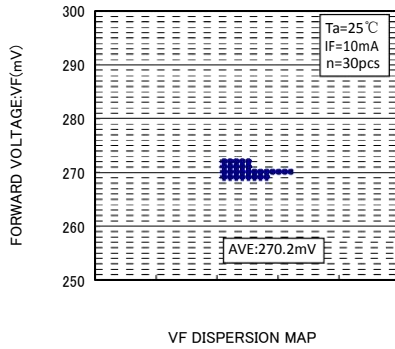
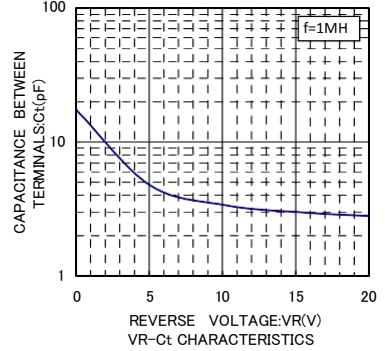
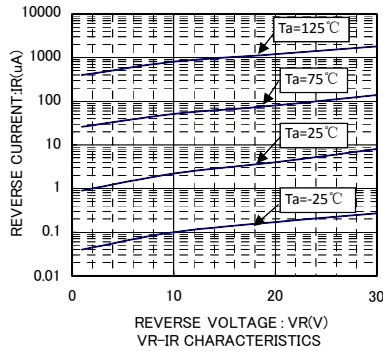
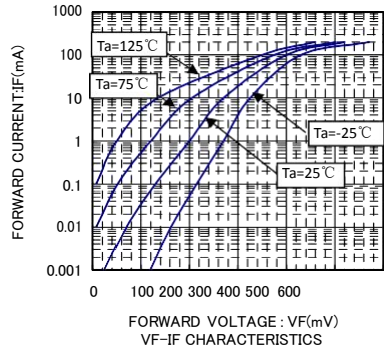
• Absolute maximum ratings (Ta=25°C)

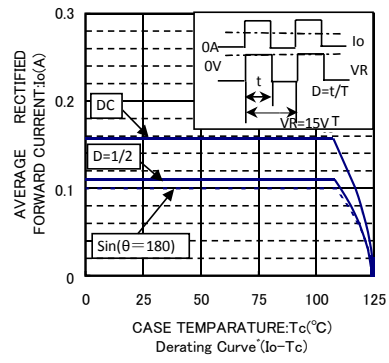
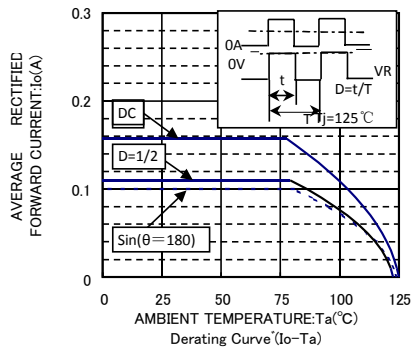
Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	I_o	100	mA
Forward current surge peak (60Hz · 1cyc)	I_{FSM}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

• Electrical characteristics (Ta=25°C)

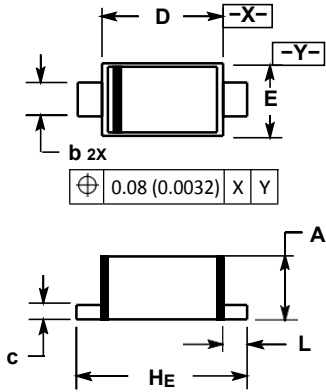
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.35	V	$I_F=10mA$
Reverse current	I_R	-	-	10	μA	$V_R=10V$

Electrical characteristic curves (Ta=25°C)





SOD-723



- NOTES:
- 1 DIMENSION IN TH AND TOLERANCE IN TH PER AS Y14.5M, 1982.
 - 2 CONTROL IN TH DIMENSION: MILLIMETER.
 - 3 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.20	0.25	0.006	0.0079	0.010

SOLDERING FOOTPRINT*

